

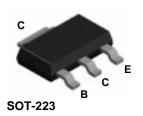
MPSA63

MMBTA63

PZTA63







PNP Darlington Transistor

This device is designed for applications requiring extremely high current gain at currents to 800 mA. Sourced from Process 61. See MPSA64 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V_{CES}	Collector-Emitter Voltage	30	V	
V _{CBO}	Collector-Base Voltage	30	V	
V_{EBO}	Emitter-Base Voltage	10	V	
I _C	Collector Current - Continuous	1.2	A	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max			Units
		MPSA63	*MMBTA63	**PZTA63	
P _D	Total Device Dissipation	625	350	1,000	mW
	Derate above 25°C	5.0	2.8	8.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3			°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

^{*}Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

These ratings are based on a maximum junction temperature of 150 degrees C.
These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

^{**}Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

PNP Darlington Transistor

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TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units	
OEE CHA	OFF CHARACTERISTICS					
				1		
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$I_C = 100 \mu A, I_B = 0$	30		V	
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 30 \text{ V}, I_{E} = 0$		100	nA	
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 10 \text{ V}, I_{C} = 0$		100	nA	
ON CHAP	RACTERISTICS*					
h _{FE}	DC Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$	5,000 10,000			

SMALL SIGNAL CHARACTERISTICS

Base-Emitter On Voltage

 $V_{\text{CE(sat)}}$

 $V_{\text{BE}(on)}$

f _T	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$	125	MHz
		f = 100 MHz		

 $I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$

Collector-Emitter Saturation Voltage I_C = 100 mA, I_B = 0.1 mA

^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

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PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
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